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# Author index


Abell, J.S., see Bi, Y.J. 166 (1996) 298
Abell, J.S., see Yang, G. 166 (1996) 820
Abrosimov, N.V., S.N. Rossolenko, V. Alex, A. Gerhardt and W. Schröder, Single crystal growth of $Si_{1-x}Ge_x$ by the Czochralski technique 166 (1996) 657
Achiba, Y., see Tachibana, M. 166 (1996) 883
Adam, J.D., see Singh, N.B. 166 (1996) 364
Adamik, M., see Hashimoto, M. 166 (1996) 792
Aggarwal, M.D., W.S. Wang, J. Choi, T. Myers, R.D. Clark, B.G. Penn, D.O. Frazier and M. Sanghadasa, Modified Bridgman–Stockbarger growth of a novel NLO organic crystal (2-methoxyphenyl)–methylene–propanedinitrile 166 (1996) 542
Aguiar, M.R. and R. Caram, Directional solidification of a Sn–Se eutectic alloy using the Bridgman–Stockbarger method 166 (1996) 398
Aguiló, M., see Solé, R. 166 (1996) 402
Åhman, J., see Bolt, R. 166 (1996) 537
Albrecht, M., see Voigt, A. 166 (1996) 694
Alex, V., see Abrosimov, N.V. 166 (1996) 657
Alexandru, H.V., C. Berbecaru, A. Grancea and V. Iov, KDP prismatic faces: kinetics and the mechanism of their growth from solutions 166 (1996) 162
Alexeev, A.N., S.Yu. Karpov, Yu.V. Pogorelsky and I.A. Sokolov, RHEED study of $c(4\times4)\rightarrow(2\times4)$ transition on GaAs(001) surface 166 (1996) 72
Alexeev, A.N., S.Yu. Karpov, M.A. Maiorov, V.E. Myachin, Yu.V. Pogorelsky and I.A. Sokolov, Thermal etching of binary and ternary III–V compounds under vacuum conditions 166 (1996) 167
Allegrini, M., see Gennari, S. 166 (1996) 309
Almgren, J., see Bolt, R. 166 (1996) 537
Althaus, M., K. Sonnenberg, E. Küssel and R. Naeven, Some new design features for vertical Bridgman furnaces and the investigation of small angle grain boundaries developed during VB growth of GaAs 166 (1996) 566
Amon, J., D. Zemke, B. Hoffmann and G. Müller, Growth of 2″ InP and GaAs crystals by the vertical gradient freeze (VGF) technique and characterization 166 (1996) 646
Anderson, T.J., see Burgess, D.R. 166 (1996) 763
Ando, H., see Kinoshita, K. 166 (1996) 266
Ando, M., see Ozawa, T. 166 (1996) 463
Ando, Y., M. Ohkohchi and M. Wang, Regrowth of carbon nanotubes and nanoparticles 166 (1996) 888
Ang, H.M., see Chan, V.A. 166 (1996) 1009
Anzawa, S., see Kinoshita, K. 166 (1996) 266
Aogaki, R., see Tadano, A. 166 (1996) 1111
Arai, K., see Shishiguchi, S. 166 (1996) 689
Arai, K., see Shimizu, T. 166 (1996) 841
Arai, Y., see Kinoshita, K. 166 (1996) 266
Ardoino, M., see Zeng, L. 166 (1996) 528
Asanuma, M., see Tadano, A. 166 (1996) 1111
Aspar, B., see Prieur, E. 166 (1996) 329
Attolini, G., see Gennari, S. 166 (1996) 309
Ausloos, M., see Stassen, S. 166 (1996) 281
Ausloos, M., see Cloots, R. 166 (1996) 816

Babanin, A., see Dmitriev, V. 166 (1996) 601
Bach, H., see Stauche, P. 166 (1996) 390
Baldochi, S.L., A.M.E. Santo, E. Martins, M. Duarte, M.M.F. Vieira, N.D. Vieira Jr. and S.P. Morato, Growth and characterization of $BaLiF_3$:TM ($Ni^{2+}$, $Co^{2+}$) for laser applications 166 (1996) 375
Baldochi, S.L., see Ranieri, I.M. 166 (1996) 423
Balibar, S., see Rolley, E. 166 (1996) 55
Banhart, F., see Konuma, M. 166 (1996) 234
Banhart, F., see Silier, I. 166 (1996) 727
Barna, A., see Hashimoto, M. 166 (1996) 792
Barna, P.B., see Hashimoto, M. 166 (1996) 792
Baronnet, A. and B. Devouard, Topology and crystal growth of natural chrysotile and polygonal serpentine 166 (1996) 952
Baruchel, J., see Prieur, E. 166 (1996) 329
Bauser, E., see Konuma, M. 166 (1996) 234
Bauser, E., see Silier, I. 166 (1996) 727
Becker, R.A., see Tanneberger, U. 166 (1996) 1074
Ben Hadid, H. and D. Henry, Numerical simulation of convective three-dimensional flows in a horizontal cylinder under the action of a constant magnetic field 166 (1996) 436
Bennema, P., On the crystallographic and statistical mechanical foundations of the forty-year old Hartman–Perdok theory 166 (1996) 17

Bennema, P., see Liu, X.Y. 166 (1996) 112
Bennema, P., see Liu, X.Y. 166 (1996) 117
Benory, E., see Weiss, E. 166 (1996) 745
Benz, K.W., see Cröll, A. 166 (1996) 239
Benz, K.W., see Eiche, C. 166 (1996) 245
Benz, K.W., see Fiederle, M. 166 (1996) 256
Benz, K.W., see Kloess, G. 166 (1996) 319
Benz, K.W., see Tegetmeier, A. 166 (1996) 651
Berbecaru, C., see Alexandru, H.V. 166 (1996) 162
Beregi, E., see Hartmann, E. 166 (1996) 109
Berends, E.M., see Domingo, C. 166 (1996) 989
Berglund, K.A., see Uusi-Penttilä, M. 166 (1996) 967
Berkstresser, G.W., see Fratello, V.J. 166 (1996) 878
Berretta, J.R., see Ranieri, I.M. 166 (1996) 423
Bersano, G., see Marino, L. 166 (1996) 1027
Bert, N., see Dmitriev, V. 166 (1996) 601
Bi, Y.J., J.S. Abell and D. Fort, Crystal growth of iron-based compounds by the cold-crucible Czochralski technique 166 (1996) 298
Bilgram, J.H., see Bisang, U. 166 (1996) 207
Bilgram, J.H., see Bisang, U. 166 (1996) 212
Bing, Y.H., see Yuan, D.R. 166 (1996) 545
Bisang, U. and J.H. Bilgram, The fractal dimension of xenon dendrites 166 (1996) 207
Bisang, U. and J.H. Bilgram, Dendritic solidification of xenon 166 (1996) 212
Blashenkov, M.N., see Nikolaev, A.E. 166 (1996) 607
Blickle, T., see Farkas, B. 166 (1996) 1064
Blouin, J., see Gerbaud, V. 166 (1996) 172
Bogatyreva, S.V., see Smolsky, I.L. 166 (1996) 228
Boilot, J.-P., see Ricolleau, C. 166 (1996) 769
Bolt, R., M. Heim, J. Almgren and J. Åhman, A high temperature study of $CsTiOAsO_4$ and $RbTiOAsO_4$ 166 (1996) 537
Bornmann, S., see Dubs, C. 166 (1996) 836
Borshchevsky, A., see Caillat, T. 166 (1996) 722
Botea, M., see Stănculescu, F. 166 (1996) 183
Brandle, C.D., see Fratello, V.J. 166 (1996) 774
Brandle, C.D., see Fratello, V.J. 166 (1996) 878
Brebrick, R.F., see Su, C.-H. 166 (1996) 736
Brener, E.A., Three-dimensional dendritic growth 166 (1996) 339
Brinkmann, M., see Stauche, P. 166 (1996) 390
Brodsky, I., see Burtman, V. 166 (1996) 832
Bruchlos, G., see Dubs, C. 166 (1996) 836
Brück, E., H.J. Gelders, B.J. Harrison and A.A. Menovsky, Laser-heated fibre pedestal growth under UHV conditions 166 (1996) 394
Bruinsma, O.S.L., see van Leeuwen, M.L.J. 166 (1996) 1004
Bulman, G., see Dmitriev, V. 166 (1996) 601
Burger, A., see Chen, K.-T. 166 (1996) 731
Burgess, D.R., P.A. Morris Hotsenpiller, T.J. Anderson and J.L. Hohman, Solid precursor MOCVD of heteroepitaxial rutile phase $TiO_2$ 166 (1996) 763
Burianek, M., J. Liebertz and M. Mühlberg, Crystal growth and characterization of $LiPbPO_4$ 166 (1996) 361
Burtman, V., M. Schieber, I. Brodsky, H. Hermon and Y. Yaroslavsky, Raman and infrared spectroscopy and transport properties of aged organometallic precursors used for the deposition of high-$T_c$ superconducting films 166 (1996) 832
Caballero, M.A., see Martínez-López, J. 166 (1996) 325
Cabré, R., see Solé, R. 166 (1996) 402
Caillat, T., J.-P. Fleurial and A. Borshchevsky, Bridgman-solution crystal growth and characterization of the skutterudite compounds $CoSb_3$ and $RhSb_3$ 166 (1996) 722
Canadell, E., see Figueras, A. 166 (1996) 798
Canselier, J.P., see Lin, C.H. 166 (1996) 104
Cao, X., see Katabi, G. 166 (1996) 760
Capelle, B., see Martínez-López, J. 166 (1996) 325
Capelle, B., see Palmier, D. 166 (1996) 347
Caram, R., see Aguiar, M.R. 166 (1996) 398
Caro, J., see Figueras, A. 166 (1996) 798
Carrà, S., S. Fogliani, M. Masi, L. Zanotti, C. Mucchino and C. Paorici, Melt–solid interface shape in LEC GaAs crystals: comparison between calculated and experimentally observed shapes 166 (1996) 641
Cavagnat, R., see Oçafrain, A. 166 (1996) 414
Chambers, J., see van Gelder, R.N.M.R. 166 (1996) 189
Chaminade, J.P., see Oçafrain, A. 166 (1996) 414
Champness, C.H., see Shukri, Z.A. 166 (1996) 708
Chan, V.A. and H.M. Ang, A laboratory continuous crystallization system for aluminium hydroxide precipitation studies 166 (1996) 1009
Chen, B.D. and J. Garside, Crystallization of tetracosane from dodecane solutions with homologous additives 166 (1996) 1094
Chen, C., see Wu, K. 166 (1996) 533
Chen, J.-C., Y.-C. Lee and C. Hu, A simple method of examining the propagation of defects in the floating-zone solidification process of lithium niobate 166 (1996) 151
Chen, K.-T., Y. Zhang, S.U. Egarievwe, M.A. George, A. Burger, C.-H. Su, Y.-G. Sha and S.L. Lehoczky, Post-growth annealing of CdS crystals grown by physical vapor transport 166 (1996) 731
Cheng, T.S., S.E. Hooper, L.C. Jenkins, C.T. Foxon, D.E. Lacklison, J.D. Dewsnip and J.W. Orton, Optical properties of doped GaN grown by a modified molecular beam epitaxial (MBE) process on GaAs substrates 166 (1996) 597
Chiampo, F., see Marmo, L. 166 (1996) 1027
Chianese, A., N. Santilli and O. Söhnel, Influence of admixtures and operating conditions on the crystallization of ammonium chloride 166 (1996) 1099

Choi, J., see Aggarwal, M.D. 166 (1996) 542
Chowdhury, A.J.S., B.M.R. Wanklyn, A.V. Volkozub and J.W. Hodby, Growth of doped and undoped BSCCO 2212 crystals in platinum crucibles by repeated remelting and recrystallisation 166 (1996) 863
Christiansen, J., see Christiansen, S. 166 (1996) 848
Christiansen, S., F. Mücke, J. Markl, W. Dorsch, R. Stark, K. Frank, H.P. Strunk, G. Saemann-Ischenko and J. Christiansen, Structural characterization of superconducting Y–Ba–Cu–O thin films, prepared by pulsed electron beam evaporation 166 (1996) 848
Cifré, J., see Figueras, A. 166 (1996) 798
Clark, R.D., see Aggarwal, M.D. 166 (1996) 542
Cloots, R., see Stassen, S. 166 (1996) 281
Cloots, R., N. Vandewalle and M. Ausloos, Simulations of the kinetic growth of $YBa_2Cu_3O_{7-\delta}$ grains 166 (1996) 816
Clydesdale, G., K.J. Roberts and R. Docherty, HABIT95 – a program for predicting the morphology of molecular crystals as a function of the growth environment 166 (1996) 78
Colônia, E.J., A.B. Dixit and N.S. Tavare, Separation of *o*- and *p*-chlorobenzoic acids: hydrotropy and precipitation 166 (1996) 976
Coriell, S.R., see Singh, N.B. 166 (1996) 364
Costa, F.E., see Ranieri, I.M. 166 (1996) 423
Courrol, L.C., see Ranieri, I.M. 166 (1996) 423
Couto, M.S., see van Enckevort, W.J.P. 166 (1996) 156
Couzi, M., see Oçafrain, A. 166 (1996) 414
Cristiani, G., see Konuma, M. 166 (1996) 234
Cröll, A., M. Schweizer, A. Tegetmeier and K.W. Benz, Floating-zone growth of GaAs 166 (1996) 239
Cröll, A., see Kloess, G. 166 (1996) 319
Cröll, A., see Tegetmeier, A. 166 (1996) 651
Czech, E., see Konuma, M. 166 (1996) 234
Czech, E., see Silier, I. 166 (1996) 727

Da, X., see Schwabe, D. 166 (1996) 483
Danilewsky, A., see Tegetmeier, A. 166 (1996) 651
Davey, R.J., J. Garside, A.M. Hilton, D. McEwan and J.W. Morrison, Emulsion solidification of meta-chloronitrobenzene: purification and crystallisation 166 (1996) 971
Derenzo, S., see Giulietti, M. 166 (1996) 1089
Derksen, A.J., see van Enckevort, W.J.P. 166 (1996) 156
De Rossi, W., see Ranieri, I.M. 166 (1996) 423
Détaint, J., see Palmier, D. 166 (1996) 347
Devouard, B., see Baronnet, A. 166 (1996) 952
DeWitt, R., see Singh, N.B. 166 (1996) 364
Dewsnip, J.D., see Cheng, T.S. 166 (1996) 597
De Yoreo, J.J., Z.U. Rek, N.P. Zaitseva and B.W. Woos, Sources of optical distortion in rapidly grown crystals of $KH_2PO_4$ 166 (1996) 291
De Yoreo, J.J., see Land, T.A. 166 (1996) 893
Díaz, F., see Solé, R. 166 (1996) 402
Diéguez, E., see Martínez-López, J. 166 (1996) 325
Dijkstra, J.W., see Kramer, H.J.M. 166 (1996) 1084
Dixit, A.B., see Colônia, E.J. 166 (1996) 976
Dmitriev, V.A., K. Irvine, G. Bulman, J. Edmond, A. Zubrilov, A.E. Nikolaev, I. Nikitina, D. Tsvetkov, A. Babanin, A. Sitnikova, Yu. Musikhin and N. Bert, Growth and characterization of GaN layers on SiC substrates 166 (1996) 601
Dmitriev, V.A., see Nikolaev, A.E. 166 (1996) 607
Docherty, R., see Clydesdale, G. 166 (1996) 78
Domingo, C., E.M. Berends and G.M. van Rosmalen, Precipitation of ultrafine benzoic acid by expansion of a supercritical carbon dioxide solution through a porous plate nozzle 166 (1996) 989
Donecker, J., B. Lux and P. Reiche, Use of optical diffraction effects in crystals for growth characterization 166 (1996) 303
Dornberger, E., W. von Ammon, N. Van den Bogaert and F. Dupret, Transient computer simulation of a CZ crystal growth process 166 (1996) 452
Dorsch, W., see Voigt, A. 166 (1996) 694
Dorsch, W., see Christiansen, S. 166 (1996) 848
Duarte, M., see Baldochi, S.L. 166 (1996) 375
Dubs, C., S. Bornmann, M. Schmelz, T. Schüler, F. Sandiumenge, G. Bruchlos and P. Görnert, Microstructure and surface morphology of *a*/*b*-axis oriented $YBa_2Cu_3O_{7-\delta}$ films on (110) $NdGaO_3$ grown by liquid phase epitaxy 166 (1996) 836
Dupret, F., see Van den Bogaert, N. 166 (1996) 446
Dupret, F., see Dornberger, E. 166 (1996) 452
Duval, W.M.B., see Singh, N.B. 166 (1996) 364

Ebling, D.G., see Eiche, C. 166 (1996) 245
Ebling, D.G., see Fiederle, M. 166 (1996) 256
Edmond, J., see Dmitriev, V. 166 (1996) 601
Egarievwe, S.U., see Chen, K.-T. 166 (1996) 731
Egorov, A.V., see Fiederle, M. 166 (1996) 256
Eiche, C., W. Joerger, M. Fiederle, D. Ebling, M. Salk, R. Schwarz and K.W. Benz, Characterization of CdTe:Cl crystals grown under microgravity conditions by time dependent charge measurements (TDCM) 166 (1996) 245
Eiche, C., see Fiederle, M. 166 (1996) 256
Emsellem, V. and P. Tabeling, On the role of convection in free dendritic growth: experimental measurement of the concentration field 166 (1996) 251
Endo, J., see Shigeta, Y. 166 (1996) 617
Erdt-Böhm, S., see Stauche, P. 166 (1996) 390

Faivre, G., Morphological instabilities of lamellar eutectic growth fronts: a survey of recent experimental and numerical results 166 (1996) 29

Fang, R., see Su, C.-H. 166 (1996) 736
Farkas, B., T. Blickle, Zs. Ulbert and M. Hasznos-Nezdei, Characterization of mixing of suspension in a mechanically stirred precipitation system 166 (1996) 1064
Feigelson, R.S., Epitaxial growth of lithium niobate thin films by the solid source MOCVD method 166 (1996) 1
Ferid, T., see Yasuda, K. 166 (1996) 612
Fiederle, M., see Eiche, C. 166 (1996) 245
Fiederle, M., C. Eiche, W. Joerger, M. Salk, A.S. Senchenkov, A.V. Egorov, D.G. Ebling and K.W. Benz, Radiation detector properties of $CdTe_{0.9}Se_{0.1}$:Cl crystals grown under microgravity in a rotating magnetic field 166 (1996) 256
Figueiredo, J.M.A., A. Vidal and O.N. Mesquita, Planar–cellular instability at a growing nematic–isotropic interface 166 (1996) 222
Figueras, A., S. Garelik, J. Caro, J. Cifré, J. Veciana, C. Rovira, E. Ribera, E. Canadell, A. Seffar and J. Fontcuberta, Preparation and characterization of conducting thin films of molecular organic conductors (TTF–TCNQ) 166 (1996) 798
Fischer, D., see Hastie, G.P. 166 (1996) 67
Fleurial, J.-P., see Caillat, T. 166 (1996) 722
Fogliani, S., see Carrà, S. 166 (1996) 641
Fontcuberta, J., see Figueras, A. 166 (1996) 798
Fornari, R., E. Gilioli, M. Moriglioni, M. Thirumavalavan and A. Zappettini, A study of iron incorporation in LEC-grown indium phosphide 166 (1996) 572
Fort, D., see Bi, Y.J. 166 (1996) 298
Foxon, C.T., see Cheng, T.S. 166 (1996) 597
Frank, K., see Christiansen, S. 166 (1996) 848
Franke, W.A., Crystal growth in silicagels in the temperature range 100°C to 250°C 166 (1996) 996
Franzosi, P., see Zeng, L. 166 (1996) 528
Fratello, V.J., H.M. O'Bryan and C.D. Brandle, Search for high thermal expansion substrates for magneto-optic thick film garnets 166 (1996) 774
Fratello, V.J., G.W. Berkstresser, C.D. Brandle and A.J. Ven Graitis, Nickel containing perovskites 166 (1996) 878
Frazier, D.O., see Aggarwal, M.D. 166 (1996) 542
Frediani, C., see Gennari, S. 166 (1996) 309
Frenkel, A., see Weiss, E. 166 (1996) 745
Fu, C.K., see Lan, C.W. 166 (1996) 458
Fujii, M., H. Iwanaga and S. Motojima, CVD growth and morphology of transition-metal phosphides 166 (1996) 99
Fujiyasu, H., see Tatsuoka, H. 166 (1996) 754
Fukuda, T., see Kawaguchi, T. 166 (1996) 489
Fukuda, T., see Kawaguchi, T. 166 (1996) 493
Fukuda, T., see Rudolph, P. 166 (1996) 578
Fukuda, T., see Schäfer, N. 166 (1996) 675
Fukuda, T., see Matsuoka, M. 166 (1996) 1035
Funayama, M., see Morita, S. 166 (1996) 370

Gabas, N., see Lin, C.H. 166 (1996) 104
Gabas, N., see Gerbaud, V. 166 (1996) 172
Gacoin, T., see Ricolleau, C. 166 (1996) 769
Gahn, C., J. Krey and A. Mersmann, The effect of impact energy and the shape of crystals on their attrition rate 166 (1996) 1058
Gandais, M., see Ricolleau, C. 166 (1996) 769
Garcia, A., see Prieur, E. 166 (1996) 329
García-Ruiz, J.M., see Moreno, A. 166 (1996) 919
Garelik, S., see Figueras, A. 166 (1996) 798
Garrett, M.H. and I. Mnushkina, Techniques for top-seeded solution growth of $BaTiO_3$ 166 (1996) 550
Garside, J., see Davey, R.J. 166 (1996) 971
Garside, J., see Mwangi, S.M. 166 (1996) 1078
Garside, J., see Chen, B.D. 166 (1996) 1094
Gärtner, G., see Müller, M. 166 (1996) 636
Gastaldi, J., see Rossberg, A. 166 (1996) 354
Gauvin, S. and J. Zyss, Growth of organic crystalline thin films, their optical characterization and application to non-linear optics 166 (1996) 507
Gay, D.H., see Rohl, A.L. 166 (1996) 84
Gedanken, A., see Katabi, G. 166 (1996) 760
Gektin, A.V., see Komar, V.K. 160 (1996) 419
Gelders, H.J., see Brück, E. 166 (1996) 394
Gennari, S., G. Attolini, C. Pelosi, P.P. Lottici, F. Riccò, M. Labardi, M. Allegrini and C. Frediani, Raman scattering study and AFM morphological characterization of MOVPE-grown (111)-strained heterostructures 166 (1996) 309
George, M.A., see Chen, K.-T. 166 (1996) 731
Gerbaud, V., N. Gabas, J. Blouin and C. Laguerie, Nucleation studies of potassium hydrogen tartrate in model solutions and wines 166 (1996) 172
Gerhardt, A., see Abrosimov, N.V. 166 (1996) 657
Gilbert, T.S., see Van Scyoc, J.M. 166 (1996) 384
Giling, L.J., see Schermer, J.J. 166 (1996) 622
Gilioli, E., see Fornari, R. 166 (1996) 572
Giulietti, M., M.M. Seckler, S. Derenzo and J.V. Valarelli, Changes in copper sulfate crystal habit during cooling crystallization 166 (1996) 1089
Glicksman, M.E., see Singh, N.B. 166 (1996) 364
Goiffon, A., see Palmier, D. 166 (1996) 347
Gomes, L., see Ranieri, I.M. 166 (1996) 423
Gómez-Morales, J., see López-Macipe, A. 166 (1996) 1015
Gómez-Morales, J., J. Torrent-Burgués, A. López-Macipe and R. Rodríguez-Clemente, Precipitation of calcium carbonate from solutions with varying $Ca^{2+}$/carbonate ratios 166 (1996) 1020
González-Mañas, M., see Martínez-López, J. 166 (1996) 325
Görnert, P., see Dubs, C. 166 (1996) 836
Gough, C.E., see Yang, G. 166 (1996) 820
Grancea, A., see Alexandru, H.V. 166 (1996) 162
Greenwood, A., see Kuznetsov, Yu.G. 166 (1996) 913

Gromilov, S., see Isaenko, L. 166 (1996) 502
Guo, J.-K., see Xia, C.-T. 166 (1996) 961
Guthmann, C., see Rolley, E. 166 (1996) 55
Gutjahr, A., see Konuma, M. 166 (1996) 234
Gutjahr, A., see Silier, I. 166 (1996) 727

Haidoux, A., see Tomasini, P. 166 (1996) 590
Hansson, P.O., see Konuma, M. 166 (1996) 234
Hansson, P.O., see Silier, I. 166 (1996) 727
Harada, J., see Itoh, Y. 166 (1996) 61
Harada, J., see Shimura, T. 166 (1996) 786
Harrison, B.J., see Brück, E. 166 (1996) 394
Hartmann, E. and E. Beregi, Dissolution forms of rare-earth orthoferrites 166 (1996) 109
Härtwig, J., see Prieur, E. 166 (1996) 329
Hasebe, K., see Shishiguchi, S. 166 (1996) 689
Hasegawa, K., S. Miyashita, H. Komatsu, C. Sano and N. Nagashima, In-situ observation of the concentration gradient layer around a growing crystal of leucine complex 166 (1996) 925
Hasegawa, M., see Zhao, T.-r. 166 (1996) 408
Hasegawa, M., see Suzuki, T. 166 (1996) 872
Hasegawa, T., W. Shimada, H. Tochihara and S. Hosoki, Dynamic observation of Si-island growth on a Si(111)-7 × 7 surface by high-temperature scanning tunneling microscopy 166 (1996) 314
Hashimoto, E., see Mizuno, K. 166 (1996) 146
Hashimoto, M., H. Qiu, T. Ohbuchi, M. Adamik, H. Nakai, A. Barna and P.B. Barna, Characterization of cobalt films grown on MgO(001) by dc-biased-sputter deposition 166 (1996) 792
Hastie, G.P., J. Johnstone, K.J. Roberts and D. Fischer, Application of polarised ultra-soft X-ray absorption near-edge spectroscopy to the characterisation of the structure of molecular interfaces 166 (1996) 67
Hasznos-Nezdei, M., see Liszi, I. 166 (1996) 179
Hasznos-Nezdei, M., see Farkas, B. 166 (1996) 1064
Hatakka, H., see Sha, Z.L. 166 (1996) 1105
Hatano, H., see Yasuda, K. 166 (1996) 612
Hayakawa, Y., see Ozawa, T. 166 (1996) 463
Heim, M., see Bolt, R. 166 (1996) 537
Henry, D., see Ben Hadid, H. 166 (1996) 436
Herden, A., see Tanneberger, U. 166 (1996) 1074
Hermon, H., see Burtman, V. 166 (1996) 832
Hibino, M., see Tanaka, S. 166 (1996) 334
Higashi, I., see Okada, S. 166 (1996) 429
Hilton, A.M., see Davey, R.J. 166 (1996) 971
Hiquily, N., see Lin, C.H. 166 (1996) 104
Hirabayashi, I., see Kitamura, T. 166 (1996) 854
Hirt, G., see Müller, M. 166 (1996) 636
Hodby, J.W., see Chowdhury, A.J.S. 166 (1996) 863
Hoffmann, B., see Amon, J. 166 (1996) 646
Hohman, J.L., see Burgess, D.R. 166 (1996) 763
Hooper, S.E., see Cheng, T.S. 166 (1996) 597
Hosoki, S., see Hasegawa, T. 166 (1996) 314
Hou, W.B., see Yuan, D.R. 166 (1996) 545
Hourai, M., see Miyano, T. 166 (1996) 469
Hourai, M., see Kanda, T. 166 (1996) 663
Hu, C., see Chen, J.-C. 166 (1996) 151
Huang, M.-H., see Huang, Y. 166 (1996) 867
Huang, Y., M.-H. Huang and J.M. Jian, Primary crystallization field and crystal growth of $Bi_2Sr_2CaCu_2O_x$ 166 (1996) 867
Huitema, E. and J.P. van der Eerden, Defect formation during crystal growth 166 (1996) 141

Ichimiya, A., see Itoh, Y. 166 (1996) 61
Iizumi, K., see Okada, S. 166 (1996) 429
Ikuhara, Y., see Kitamura, T. 166 (1996) 854
Imaeda, M., see Kawaguchi, T. 166 (1996) 489
Imaeda, M., see Kawaguchi, T. 166 (1996) 493
Imai, M., see Shiraishi, Y. 166 (1996) 685
Inami, S.-i., see Miyano, T. 166 (1996) 469
Instone, T., see van Gelder, R.N.M.R. 166 (1996) 189
Iov, V., see Alexandru, H.V. 166 (1996) 162
Irvine, K., see Dmitriev, V. 166 (1996) 601
Isaenko, L., A. Merkulov, V. Tyurikov, R. Mashkovtsev and S. Gromilov, Growth and characterization of $KTi_{1-x}Zr_xAsO_5$ single crystals 166 (1996) 502
Ishikawa, T., see Tanaka, S. 166 (1996) 334
Itoh, Y., I. Takahashi, A. Ichimiya, J. Harada and N.S. Sokolov, Structure of $CaF_2$/Si(111) long interface 166 (1996) 61
Ivanov, N.P., see Komar, V.K. 160 (1996) 419
Ivantsov, V.A., see Nikolaev, A.E. 166 (1996) 607
Iwami, M., see Mizuno, K. 166 (1996) 146
Iwanaga, H., see Fujii, M. 166 (1996) 99
Izmailov, A.F. and A.S. Myerson, Relationship between solution shear viscosity and density at the saturation point 166 (1996) 261
Izmailov, A.F., see Myerson, A.S. 166 (1996) 981

James, R.B., see Van Scyoc, J.M. 166 (1996) 384
Jenichen, B., see Silier, I. 166 (1996) 727
Jenkins, L.C., see Cheng, T.S. 166 (1996) 597
Jian, J.M., see Huang, Y. 166 (1996) 867
Jiang, H., see Yu, X. 166 (1996) 195
Jiang, M.H., see Yuan, D.R. 166 (1996) 545
Jitsukawa, H., see Matsushita, H. 166 (1996) 712
Joerger, W., see Eiche, C. 166 (1996) 245
Joerger, W., see Fiederle, M. 166 (1996) 256
Johnstone, J., see Hastie, G.P. 166 (1996) 67
Jones, I.P., see Yang, G. 166 (1996) 820
Juang, W.-S., see Tai, C.Y. 166 (1996) 1040
Juravel, Y., see Weiss, E. 166 (1996) 745
Jurisch, M., see Müller, M. 166 (1996) 636

Kaldis, E., see Rossberg, A. 166 (1996) 354
Kamiko, M., see Mogi, I. 166 (1996) 276
Kanda, I., T. Suzuki and K. Kojima, Influence of crucible and crystal rotation on oxygen-concentration distribution in large-diameter silicon single crystals 166 (1996) 669

Kanda, T., see Miyano, T. 166 (1996) 469

Kanda, T., M. Hourai, S. Miki, T. Shigematsu, H. Tomokage, T. Miyano, H. Morita and A. Shintani, Influence of melt-temperature fluctuations on striation formation in large-scale Czochralski Si growth systems 166 (1996) 663

Karpov, S.Yu., see Alexeev, A.N. 166 (1996) 72

Karpov, S.Yu., see Alexeev, A.N. 166 (1996) 167

Katabi, G., Yu. Koltypin, X. Cao and A. Gedanken, Self-assembled monolayer coatings of iron nanoparticles with thiol derivatives 166 (1996) 760

Kato, Takashi, see Kuriyama, K. 166 (1996) 631

Kato, Tomoharu, see Kuriyama, K. 166 (1996) 631

Kawaguchi, T., M. Imaeda, M. Minakata, T. Taniuchi and T. Fukuda, Growth of $LiNbO_3/LiNb_{1-x}Ta_xO_3$ multilayered waveguides on $LiNbO_3$ by liquid phase epitaxy 166 (1996) 489

Kawaguchi, T., M. Imaeda, R. Ohuchi, M. Minakata, T. Taniuchi and T. Fukuda, Growth-temperature dependence of the Li/Nb ratio in LPE-grown $LiNbO_3$ films estimated by second-harmonic generation 166 (1996) 493

Kawamoto, K., see Yasuda, K. 166 (1996) 612

Kawarai, K., see Sugino, T. 166 (1996) 628

Kedar, E., see Weiss, E. 166 (1996) 745

Kikuchi, K., see Tachibana, M. 166 (1996) 883

Kino, T., see Mizuno, K. 166 (1996) 146

Kinoshita, K., S. Yoda, T. Nakamura, H. Sameshima, H. Ando, S. Anzawa and Y. Arai, Video imaging of the melting and solidification processes of the $PbBr_2$–$PbCl_2$ system under microgravity 166 (1996) 266

Kitamura, T., Y. Yamada, Y. Shiohara, I. Hirabayashi, S. Tanaka, Y. Sugawara and Y. Ikuhara, Growth mechanism and crystalline orientation of liquid-phase epitaxially grown $YBa_2Cu_3O_{7-y}$ films 166 (1996) 854

Kitano, M., T. Okabe and M. Shiojiri, Morphology and growth mechanism of ZnO particles electro-crystallized on Zn in aqueous solution 166 (1996) 1116

Klapper, H., see Tanneberger, U. 166 (1996) 1074

Kloess, G., A. Cröll and K.W. Benz, Contactless measurement of dopant distribution using etch roughnesses 166 (1996) 319

Koh, H.J., see Rudolph, P. 166 (1996) 578

Koh, H.J., see Schäfer, N. 166 (1996) 675

Köhler, A., see Müller, M. 166 (1996) 636

Köhler, R., see Silier, I. 166 (1996) 727

Kojima, K., see Kanda, I. 166 (1996) 669

Kojima, K., see Tachibana, M. 166 (1996) 883

Koltypin, Yu., see Katabi, G. 166 (1996) 760

Komar, V.K., A.V. Gektin, N.P. Ivanov, Y.A. Nesterenko and N.V. Shiran, Growth and study of properties of pure and rare-earth-doped $KMgF_3$ crystals 160 (1996) 419

Komatsu, H., see Kurihara, K. 166 (1996) 904

Komatsu, H., see Hasegawa, K. 166 (1996) 925

Konuma, M., I. Silier, A. Gutjahr, P.O. Hansson, G. Cristiani, E. Czech, E. Bauser and F. Banhart, Centrifugal techniques for solution growth of semiconductor layers 166 (1996) 234

Konuma, M., see Silier, I. 166 (1996) 727

Koshimae, T., see Obara, K. 166 (1996) 271

Kouta, H. and Y. Kuwano, β-$BaB_2O_4$ phase-matching-direction growth by the Czochralski method 166 (1996) 497

Kramer, H.J.M., see Ó Meadhra, R. 166 (1996) 1046

Kramer, H.J.M., J.W. Dijkstra, A.M. Neumann, R. Ó Meadhra and G.M. van Rosmalen, Modelling of industrial crystallizers, a compartmental approach using a dynamic flowsheeting tool 166 (1996) 1084

Krämer, V., see Weise, S. 166 (1996) 718

Krauns, C., see Yamada, Y. 166 (1996) 804

Krauns, C., see Nakamura, M. 166 (1996) 859

Kreuwel, K.B.G., see van Enckevort, W.J.P. 166 (1996) 156

Krey, J., see Gahn, C. 166 (1996) 1058

Krinke, J., see Voigt, A. 166 (1996) 694

Kubo, Y., see Obara, K. 166 (1996) 271

Kudaka, K., see Okada, S. 166 (1996) 429

Kudou, K., see Okada, S. 166 (1996) 429

Kuech, T.F. and N.R. Perkins, Metalorganic vapor phase epitaxy of II–VI materials for visible light emitters 166 (1996) 558

Kumagawa, M., see Ozawa, T. 166 (1996) 463

Kurihara, K., S. Miyashita, G. Sazaki, T. Nakada, Y. Suzuki and H. Komatsu, Interferometric study on the crystal growth of tetragonal lysozyme crystal 166 (1996) 904

Kuriyama, K., Takashi Kato, Tomoharu Kato and H. Matsuno, Growth and photoluminescence properties of the filled tetrahedral semiconductor LiZnAs 166 (1996) 631

Kurosaka, S., see Shiraishi, Y. 166 (1996) 685

Küssel, E., see Althaus, M. 166 (1996) 566

Kuwabara, H., see Tatsuoka, H. 166 (1996) 754

Kuwano, Y., see Kouta, H. 166 (1996) 497

Kuznetsov, Yu.G., see Land, T.A. 166 (1996) 893

Kuznetsov, Yu.G., A.J. Malkin, A. Greenwood and A. McPherson, Michelson interferometric studies of protein and virus crystal growth 166 (1996) 913

Labardi, M., see Gennari, S. 166 (1996) 309

Lacklison, D.E., see Cheng, T.S. 166 (1996) 597

Lacmann, R., see Tanneberger, U. 166 (1996) 1074

Laguerie, C., see Gerbaud, V. 166 (1996) 172

Lan, C.W., M.C. Liang, C.R. Song and C.K. Fu, Shape control in crystal pulling from a floating die 166 (1996) 458
Land, T.A., A.J. Malkin, Yu.G. Kuznetsov, A. McPherson and J.J. De Yoreo, Mechanisms of protein and virus crystal growth: an atomic force microscopy study of canavalin and STMV crystallization 166 (1996) 893
Lee, Y.-C., see Chen, J.-C. 166 (1996) 151
Lehoczky, S.L., see Chen, K.-T. 166 (1996) 731
Lehoczky, S.L., see Su, C.-H. 166 (1996) 736
Lei, X.-Y., P. Wan, Q.-H. Wei, C.-H. Zhou and N.-B. Ming, Nucleation and growth of drop-like clusters in two-dimensional colloidal systems 166 (1996) 909
Lenz, A., see Weise, S. 166 (1996) 718
Leusen, F.J.J., Ab initio prediction of polymorphs 166 (1996) 900
Liang, M.C., see Lan, C.W. 166 (1996) 458
Liebertz, J., see Burianek, M. 166 (1996) 361
Lin, C.H., N. Gabas, J.P. Canselier and N. Hiquily, Influence of additives on the growth morphology of γ-aminobutyric acid 166 (1996) 104
Liszi, I. and M. Hasznos-Nezdei, Crystal growth of (E)-2-butenedioic acid from aqueous solution in batch-cooling crystallization 166 (1996) 179
Liu, H.-C., see Su, C.-H. 166 (1996) 736
Liu, M.G., see Yuan, D.R. 166 (1996) 545
Liu, X.Y. and P. Bennema, An inhomogeneous cell model and the growth of crystals 166 (1996) 112
Liu, X.Y. and P. Bennema, Prediction of the growth morphology of crystals 166 (1996) 117
López-Macipe, A., J. Gómez-Morales and R. Rodríguez-Clemente, Calcium carbonate precipitation from aqueous solutions containing Aerosol OT 166 (1996) 1015
López-Macipe, A., see Gómez-Morales, J. 166 (1996) 1020
Lottici, P.P., see Gennari, S. 166 (1996) 309
Louhi-Kultanen, M., see Sha, Z.L. 166 (1996) 1105
Lundström, T., see Okada, S. 166 (1996) 429
Lux, B., see Donecker, J. 166 (1996) 303

Maeda, M., see Sugino, T. 166 (1996) 628
Maejima, T., see Yasuda, K. 166 (1996) 612
Magerl, A., see Rossberg, A. 166 (1996) 354
Maiorov, M.A., see Alexeev, A.N. 166 (1996) 167
Maki, K., see Shigeta, Y. 166 (1996) 617
Malkin, A.J., see Land, T.A. 166 (1996) 893
Malkin, A.J., see Kuznetsov, Yu.G. 166 (1996) 913
Mani, S.S., see Singh, N.B. 166 (1996) 364
Manna, L., see Marmo, L. 166 (1996) 1027
Manth, T., D. Mignon and H. Offermann, The role of hydrodynamics in precipitation 166 (1996) 998
Markl, J., see Christiansen, S. 166 (1996) 848
Marmo, L., L. Manna, F. Chiampo, S. Sicardi and G. Bersano, Influence of mixing on the particle size distribution of an organic precipitate 166 (1996) 1027
Marten, R., see Seidl, A. 166 (1996) 680
Martínez-López, J., M. González-Mañas, M.A. Caballero, E. Diéguez and B. Capelle, Synchrotron X-ray topography of bismuth silicon oxide crystals 166 (1996) 325
Martins, E., see Baldochi, S.L. 166 (1996) 375
Mashkovtsev, R., see Isaenko, L. 166 (1996) 502
Masi, M., see Carrà, S. 166 (1996) 641
Matsuno, H., see Kuriyama, K. 166 (1996) 631
Matsuoka, M., T. Fukuda, Y. Takagi and H. Takiyama, Purification of organic solid solutions by melt crystallization: comparison between layer and suspension crystallization 166 (1996) 1035
Matsushita, H., H. Jitsukawa and T. Takizawa, Thermal analysis of the chemical-reaction process for $CuGa_{1-x}In_xSe_2$ crystals 166 (1996) 712
Maurin, M., see Tomasini, P. 166 (1996) 590
Mazuruk, K., see Su, C.-H. 166 (1996) 736
McEwan, D., see Davey, R.J. 166 (1996) 971
McPherson, A., see Land, T.A. 166 (1996) 893
McPherson, A., see Kuznetsov, Yu.G. 166 (1996) 913
Menovsky, A.A., see Brück, E. 166 (1996) 394
Merkulov, A., see Isaenko, L. 166 (1996) 502
Mersmann, A., see Gahn, C. 166 (1996) 1058
Mersmann, A., see Tanneberger, U. 166 (1996) 1074
Mesquita, O.N., see Figueiredo, J.M.A. 166 (1996) 222
Meyer, S. and A.G. Ostrogorsky, Interface shape in the vertical Bridgman configuration with and without the submerged heater 166 (1996) 700
Michiyama, M., see Tachibana, M. 166 (1996) 883
Mignon, D., see Manth, T. 166 (1996) 998
Miki, S., see Kanda, T. 166 (1996) 663
Minakata, M., see Kawaguchi, T. 166 (1996) 489
Minakata, M., see Kawaguchi, T. 166 (1996) 493
Minamide, M., see Yasuda, K. 166 (1996) 612
Ming, N.-B., see Lei, X.-Y. 166 (1996) 909
Misaki, H., see Shimura, T. 166 (1996) 786
Miyano, T., S.-i. Inami, A. Shintani, T. Kanda and M. Hourai, Dynamical behaviour of Czochralski melts and its influence on crystal growth 166 (1996) 469
Miyano, T., see Kanda, T. 166 (1996) 663
Miyashita, S., see Kurihara, K. 166 (1996) 904
Miyashita, S., see Hasegawa, K. 166 (1996) 925
Miyazawa, S., see Sasaura, M. 166 (1996) 825
Miyazawa, Y., S. Morita and H. Sekiwa, Flow in oxide melts in a high magnetic field 166 (1996) 286
Miyazawa, Y., see Morita, S. 166 (1996) 370
Mizuno, K., A. Tamiya, K. Ono, M. Iwami, E. Hashimoto and T. Kino, Vacancy-type dislocation loops observed at fairly high temperatures in nearly perfect Al crystals 166 (1996) 146
Mnushkina, I., see Garrett, M.H. 166 (1996) 550
Mogi, I. and M. Kamiko, Striking effects of magnetic field on the growth morphology of electrochemical deposits 166 (1996) 276
Moldoveanu, M., see Stănculescu, F. 166 (1996) 183

Momonaga, M., J. Stávek and J. Ulrich, Interpretation of dissolution rates by the reaction fractal dimensions 166 (1996) 1053
Morato, S.P., see Baldochi, S.L. 166 (1996) 375
Morato, S.P., see Ranieri, I.M. 166 (1996) 423
Moreno, A., D. Rondón and J.M. García-Ruiz, Growth of shaped single crystals of proteins 166 (1996) 919
Moriglioni, M., see Fornari, R. 166 (1996) 572
Morita, H., see Kanda, T. 166 (1996) 663
Morita, S., see Miyazawa, Y. 166 (1996) 286
Morita, S., T. Watanabe, M. Funayama, Y. Miyazawa and M. Sekita, The growth of $(Tb_xGd_{1-x})AlO_3$ single crystals by the Czochralski method 166 (1996) 370
Morris Hotsenpiller, P.A., see Burgess, D.R. 166 (1996) 763
Morris Hotsenpiller, P.A., G.A. Wilson, A. Roshko, J.B. Rothman and G.S. Rohrer, Heteroepitaxial growth of $TiO_2$ films by ion-beam sputter deposition 166 (1996) 779
Morrison, J.W., see Davey, R.J. 166 (1996) 971
Motojima, S., see Fujii, M. 166 (1996) 99
Mucchino, C., see Carrà, S. 166 (1996) 641
Mücke, F., see Christiansen, S. 166 (1996) 848
Mühlberg, M., see Burianek, M. 166 (1996) 361
Müller, G., see Müller, M. 166 (1996) 636
Müller, G., see Amon, J. 166 (1996) 646
Müller, G., see Seidl, A. 166 (1996) 680
Müller, M., G. Gärtner, G. Hirt, M. Jurisch, A. Köhler, G. Müller and B. Weinert, Control of oxygen in undoped liquid encapsulation Czochralski GaAs 166 (1996) 636
Musikhin, Yu., see Dmitriev, V. 166 (1996) 601
Mwangi, S.M. and J. Garside, Morphology of 6-aminopenicillanic acid crystals and the effect of phenoxyacetic acid 166 (1996) 1078
Myachin, V.E., see Alexeev, A.N. 166 (1996) 167
Myers, T., see Aggarwal, M.D. 166 (1996) 542
Myerson, A.S., see Izmailov, A.F. 166 (1996) 261
Myerson, A.S., A.F. Izmailov and H.-S. Na, Thermodynamic studies of levitated microdroplets of highly supersaturated electrolyte solutions 166 (1996) 981

Na, H.-S., see Myerson, A.S. 166 (1996) 981
Naeven, R., see Althaus, M. 166 (1996) 566
Nagashima, N., see Sano, C. 166 (1996) 129
Nagashima, N., see Hasegawa, K. 166 (1996) 925
Nagel, N., see Silier, I. 166 (1996) 727
Nakada, T., see Kurihara, K. 166 (1996) 904
Nakai, H., see Hashimoto, M. 166 (1996) 792
Nakamura, M., see Yamada, Y. 166 (1996) 804
Nakamura, M., C. Krauns, Y. Yamada and Y. Shiohara, Crystal growth of $SmBa_2Cu_3O_{7-x}$ under low oxygen partial pressure 166 (1996) 859
Nakamura, T., see Kinoshita, K. 166 (1996) 266
Nakamura, T., see Tatsuoka, H. 166 (1996) 754
Nakanishi, Y., see Tatsuoka, H. 166 (1996) 754
Nesterenko, Y.A., see Komar, V.K. 160 (1996) 419
Neumann, A.M., see Kramer, H.J.M. 166 (1996) 1084
Nikitina, I., see Dmitriev, V. 166 (1996) 601
Nikolaev, V., see Dmitriev, V. 166 (1996) 601
Nikolaev, A.E., V.A. Ivantsov, S.V. Rendakova, M.N. Blashenkov and V.A. Dmitriev, SiC liquid-phase epitaxy on patterned substrates 166 (1996) 607
Nikolov, V., see Solé, R. 166 (1996) 402
Nishinaga, T., see Ren, H.-W. 166 (1996) 217
Nogueira, G.E.C., see Ranieri, I.M. 166 (1996) 423
Nonaka, H., see Shimizu, T. 166 (1996) 841
Nowak, E., see Weise, S. 166 (1996) 718

Obara, K., Collective behaviour of metastable liquid particles layer on liquid surface 166 (1996) 124
Obara, K., Y. Ohtera and Y. Suemoto, Two-dimensional metastable macro-crystals of liquid particles on a liquid surface 166 (1996) 136
Obara, K., T. Koshimae, Y. Kubo and Y. Suemoto, Kinetics of microclusters in nonequilibrium plasma magnetron sputtering 166 (1996) 271
O'Bryan, H.M., see Fratello, V.J. 166 (1996) 774
Oçafrain, A., J.P. Chaminade, O. Viraphong, R. Cavagnat, M. Couzi and M. Pouchard, Growth by the heat exchanger method and characterization of neighborite, $NaMgF_3$ 166 (1996) 414
Offermann, H., see Manth, T. 166 (1996) 998
Ohbuchi, T., see Hashimoto, M. 166 (1996) 792
Ohkohchi, M., see Ando, Y. 166 (1996) 888
Ohler, M., see Prieur, E. 166 (1996) 329
Ohtera, Y., see Obara, K. 166 (1996) 136
Ohuchi, R., see Kawaguchi, T. 166 (1996) 493
Oka, K., H. Unoki, H. Yamaguchi and H. Takahashi, Crystal growth of $PbTiO_3$ by the top-seeded solution-growth method 166 (1996) 380
Okabe, T., see Kitano, M. 166 (1996) 1116
Okada, S., K. Kudou, K. Iizumi, K. Kudaka, I. Higashi and T. Lundström, Single-crystal growth and properties of CrB, $Cr_3B_4$, $Cr_2B_3$ and $CrB_2$ from high-temperature aluminum solutions 166 (1996) 429
Okamoto, T., see Shishiguchi, S. 166 (1996) 689
Okui, N., see Yase, K. 166 (1996) 942
Ó Meadhra, R., H.J.M. Kramer and G.M. van Rosmalen, Crystallization kinetics of pentaerythritol 166 (1996) 1046
Ó Meadhra, R., see Kramer, H.J.M. 166 (1996) 1084
Ono, K., see Mizuno, K. 166 (1996) 146
Orton, J.W., see Cheng, T.S. 166 (1996) 597
Oshita, M., see Tatsuoka, H. 166 (1996) 754
Ostrogorsky, A.G., see Meyer, S. 166 (1996) 700
Ozawa, T., M. Ando, Y. Hayakawa and M. Kumagawa, InGaAs mixed crystals grown by the temperature-difference method and the numerical analysis of solution convection 166 (1996) 463

Palmier, D., A. Goiffon, B. Capelle, J. Détaint and E. Philippot, Crystal growth and characterizations of quartz-like material: gallium phosphate ($GaPO_4$) 166 (1996) 347
Palosaari, S., see Sha, Z.L. 166 (1996) 1105
Paorici, C., see Zeng, L. 166 (1996) 528
Paorici, C., see Carrà, S. 166 (1996) 641
Parkinson, G.M., see Reyhani, M.M. 166 (1996) 1068
Pelosi, C., see Gennari, S. 166 (1996) 309
Penn, B.G., see Aggarwal, M.D. 166 (1996) 542
Perkins, N.R., see Kuech, T.F. 166 (1996) 558
Philippot, E., see Palmier, D. 166 (1996) 347
Piechotka, M., see Rossberg, A. 166 (1996) 354
Pogorelsky, Yu.V., see Alexeev, A.N. 166 (1996) 72
Pogorelsky, Yu.V., see Alexeev, A.N. 166 (1996) 167
Porowski, S., High pressure growth of GaN – new prospects for blue lasers 166 (1996) 583
Pouchard, M., see Oçafrain, A. 166 (1996) 414
Prasad, V., see Zou, Y.F. 166 (1996) 476
Prieur, E., J. Härtwig, A. Garcia, M. Ohler, J. Baruchel, B. Aspar and G. Rolland, Synchrotron white beam topographic investigation of crystalline defects in silicon on insulator materials 166 (1996) 329

Qiu, H., see Hashimoto, M. 166 (1996) 792

Raidt, H., see Silier, I. 166 (1996) 727
Ranieri, I.M., S.L. Baldochi, A.M.E. Santo, L. Gomes, L.C. Courrol, L.V.G. Tarelho, W. de Rossi, J.R. Berretta, F.E. Costa, G.E.C. Nogueira, N.U. Wetter, D.M. Zezell, N.D. Vieira, Jr. and S.P. Morato, Growth of $LiYF_4$ crystals doped with holmium, erbium and thulium 166 (1996) 423
Reiche, P., see Donecker, J. 166 (1996) 303
Rek, Z.U., see De Yoreo, J.J. 166 (1996) 291
Ren, H.-W., X.-Q. Shen and T. Nishinaga, In situ observation of macrostep formation on misoriented GaAs(111)B by molecular beam epitaxy 166 (1996) 217
Rendakova, S.V., see Nikolaev, A.E. 166 (1996) 607
Reyhani, M.M. and G.M. Parkinson, A comparison of secondary nuclei produced by contact of different growth faces of potash alum crystals under supersaturated solutions 166 (1996) 1068
Ribera, E., see Figueras, A. 166 (1996) 798
Riccò, F., see Gennari, S. 166 (1996) 309
Ricolleau, C., M. Gandais, T. Gacoin and J.-P. Boilot, Correlation between structural and optical properties of PbS nanocrystals 166 (1996) 769
Roberts, K.J., see Hastie, G.P. 166 (1996) 67
Roberts, K.J., see Clydesdale, G. 166 (1996) 78
Roberts, K.J., see van Gelder, R.N.M.R. 166 (1996) 189
Rodríguez-Clemente, R., see López-Macipe, A. 166 (1996) 1015
Rodríguez-Clemente, R., see Gómez-Morales, J. 166 (1996) 1020
Rohl, A.L. and D.H. Gay, Calculating the effects of surface relaxation on morphology 166 (1996) 84
Rohrer, G.S., see Morris Hotsenpiller, P.A. 166 (1996) 779
Rolland, G., see Prieur, E. 166 (1996) 329
Rolley, E., C. Guthmann and S. Balibar, Vicinal surfaces of helium 4 crystals 166 (1996) 55
Rondón, D., see Moreno, A. 166 (1996) 919
Rosenberger, F., Protein crystallization 166 (1996) 40
Roshko, A., see Morris Hotsenpiller, P.A. 166 (1996) 779
Rossberg, A., M. Piechotka, G. Wetzel, J. Gastaldi, A. Magerl and E. Kaldis, Structural non-uniformities in mercuric iodide crystals grown by two different vapour growth techniques 166 (1996) 354
Rossolenko, S.N., see Abrosimov, N.V. 166 (1996) 657
Rothman, J.B., see Morris Hotsenpiller, P.A. 166 (1996) 779
Rovira, C., see Figueras, A. 166 (1996) 798
Rudneva, E.B., see Smolsky, I.L. 166 (1996) 228
Rudolph, P., H.J. Koh, N. Schäfer and T. Fukuda, The crystal perfection depends on the superheating of the mother phase too – experimental facts and speculations on the "melt structure" of semiconductor compounds 166 (1996) 578
Ruiz, X., see Solé, R. 166 (1996) 402
Rulmont, A., see Stassen, S. 166 (1996) 281

Saemann-Ischenko, G., see Christiansen, S. 166 (1996) 848
Saijo, H. and M. Shiojiri, J-aggregates of cyanine dye molecules adsorbed on AgBr emulsion crystal surfaces 166 (1996) 930
Sakuma, H., see Tachibana, M. 166 (1996) 883
Salk, M., see Eiche, C. 166 (1996) 245
Salk, M., see Fiederle, M. 166 (1996) 256
Sameshima, H., see Kinoshita, K. 166 (1996) 266
Sandiumenge, F., see Dubs, C. 166 (1996) 836
Sanghadasa, M., see Aggarwal, M.D. 166 (1996) 542
Sano, C. and N. Nagashima, Effects of L-glutamyl peptides on the growth of L-glutamic acid crystals (α-form) 166 (1996) 129
Sano, C., see Hasegawa, K. 166 (1996) 925
Santilli, N., see Chianese, A. 166 (1996) 1099
Santo, A.M.E., see Baldochi, S.L. 166 (1996) 375
Santo, A.M.E., see Ranieri, I.M. 166 (1996) 423
Santoro, G.J., see Singh, N.B. 166 (1996) 364
Sasaura, M. and S. Miyazawa, Growth instability in $LnSrGaO_4$ (Ln: Pr,Nd) crystal pulling 166 (1996) 825
Sazaki, G., see Kurihara, K. 166 (1996) 904
Schäfer, N., see Rudolph, P. 166 (1996) 578
Schäfer, N., T. Yamada, K. Shimamura, H.J. Koh and T. Fukuda, Growth of $Si_xGe_{1-x}$ crystals by the micro-pulling-down method 166 (1996) 675
Scharmann, A., see Schwabe, D. 166 (1996) 483
Schermer, J.J., W.J.P. van Enckevort and L.J. Giling, Surface stabilization phenomena on flame-deposited diamond single crystals 166 (1996) 622

Schieber, M., see Van Scyoc, J.M. 166 (1996) 384
Schieber, M., see Burtman, V. 166 (1996) 832
Schlesinger, T.E., see Van Scyoc, J.M. 166 (1996) 384
Schmelz, M., see Dubs, C. 166 (1996) 836
Schmiemann, D., see Tanneberger, U. 166 (1996) 1074
Schröder, W., see Abrosimov, N.V. 166 (1996) 657
Schüler, T., see Dubs, C. 166 (1996) 836
Schumann, B., see Weise, S. 166 (1996) 718
Schwabe, D., X. Da and A. Scharmann, Unstable flow and solidification speed due to the interaction of thermocapillary and solutocapillary forces in directional solidification 166 (1996) 483
Schwarz, R., see Eiche, C. 166 (1996) 245
Schweizer, M., see Cröll, A. 166 (1996) 239
Seckler, M.M., see Giulietti, M. 166 (1996) 1089
Seffar, A., see Figueras, A. 166 (1996) 798
Seidl, A., R. Marten and G. Müller, In situ investigation of oxygen distribution and transport in Czochralski silicon melts by electrochemical solid ionic sensors 166 (1996) 680
Sekita, M., see Morita, S. 166 (1996) 370
Sekiwa, H., see Miyazawa, Y. 166 (1996) 286
Senchenkov, A.S., see Fiederle, M. 166 (1996) 256
Sha, Y.-G., see Chen, K.-T. 166 (1996) 731
Sha, Y.-G., see Su, C.-H. 166 (1996) 736
Sha, Z.L., H. Hatakka, M. Louhi-Kultanen and S. Palosaari, Crystallization kinetics of potassium sulfate in an MSMPR stirred crystallizer 166 (1996) 1105
Shang, P., see Yang, G. 166 (1996) 820
Shen, X.-Q., see Ren, H.-W. 166 (1996) 217
Shi, E.-W., see Xia, C.-T. 166 (1996) 961
Shigematsu, N., see Shishiguchi, S. 166 (1996) 689
Shigematsu, T., see Kanda, T. 166 (1996) 663
Shigeta, Y., J. Endo and K. Maki, A characteristic feature of crystalline thin-film growth of Si on a $7 \times 7$ superlattice surface of Si(111) 166 (1996) 617
Shih, C.-Y., see Tai, C.Y. 166 (1996) 1040
Shimada, W., see Hasegawa, T. 166 (1996) 314
Shimamura, K., see Schäfer, N. 166 (1996) 675
Shimizu, T., H. Nonaka and K. Arai, Growth of homoepitaxial $YBa_2Cu_3O_{7-x}$ films by molecular beam epitaxy 166 (1996) 841
Shimura, T., H. Misaki, M. Umeno, I. Takahashi and J. Harada, X-ray diffraction evidence for the existence of epitaxial microcrystallites in thermally oxidized $SiO_2$ thin films on Si(111) surfaces 166 (1996) 786
Shintani, A., see Miyano, T. 166 (1996) 469
Shintani, A., see Kanda, T. 166 (1996) 663
Shiohara, Y., see Yamada, Y. 166 (1996) 804
Shiohara, Y., see Kitamura, T. 166 (1996) 854
Shiohara, Y., see Nakamura, M. 166 (1996) 859
Shiojiri, M., see Saijo, H. 166 (1996) 930
Shiojiri, M., see Tanabe, K. 166 (1996) 935
Shiojiri, M., see Kitano, M. 166 (1996) 1116
Shirafuji, J., see Sugino, T. 166 (1996) 628
Shiraishi, Y., S. Kurosaka and M. Imai, Silicon crystal growth using a liquid-feeding Czochralski method 166 (1996) 685
Shiran, N.V., see Komar, V.K. 160 (1996) 419
Shishiguchi, S., T. Okamoto, K. Arai, K. Hasebe and N. Shigematsu, The reduction of grain size in LPCVD poly-Si by in situ oxygen and phosphorus doping 166 (1996) 689
Shukri, Z.A. and C.H. Champness, Identification of oxygen in the copper as the source of adhesion in Bridgman-grown $CuInSe_2$ crystals 166 (1996) 708
Sicardi, S., see Marmo, L. 166 (1996) 1027
Silier, I., see Konuma, M. 166 (1996) 234
Silier, I., A. Gutjahr, N. Nagel, P.O. Hansson, E. Czech, M. Konuma, E. Bauser, F. Banhart, R. Köhler, H. Raidt and B. Jenichen, Solution growth of epitaxial semiconductor-on-insulator layers 166 (1996) 727
Singh, N.B., S.S. Mani, J.D. Adam, S.R. Coriell, M.E. Glicksman, W.M.B. Duval, G.J. Santoro and R. DeWitt, Direct observations of interface instabilities 166 (1996) 364
Sitnikova, A., see Dmitriev, V. 166 (1996) 601
Smolsky, I.L., N.P. Zaitseva, E.B. Rudneva and S.V. Bogatyreva, Formation of "hair" inclusions in rapidly grown potassium dihydrogen phosphate crystals 166 (1996) 228
Söhnel, O., see Chianese, A. 166 (1996) 1099
Sokolov, I.A., see Alexeev, A.N. 166 (1996) 72
Sokolov, I.A., see Alexeev, A.N. 166 (1996) 167
Sokolov, N.S., see Itoh, Y. 166 (1996) 61
Solé, R., X. Ruiz, R. Cabré, M. Aguiló, F. Díaz and V. Nikolov, Co and Sn substituted barium M-hexaferrites: single crystal growth and magnetic characterization 166 (1996) 402
Song, C.R., see Lan, C.W. 166 (1996) 458
Sonnenberg, K., see Althaus, M. 166 (1996) 566
Stănculescu, F., M. Moldoveanu and M. Botea, Analysis of the mechanism of diffusion limited oxygen precipitation in Cz-silicon 166 (1996) 183
Stark, R., see Christiansen, S. 166 (1996) 848
Stassen, S., A. Vanderschueren, R. Cloots, A. Rulmont and M. Ausloos, Texturation of Bi-based 2212 superconducting bulk ceramics 166 (1996) 281
Stauche, P., S. Erdt-Böhm, M. Brinkmann and H. Bach, Crystal growth and characterization of $Fe_{2+x}Ti_{1-x}$ 166 (1996) 390
Stávek, J., see Momonaga, M. 166 (1996) 1053
Steiner, B., see Voigt, A. 166 (1996) 694
Strunk, H.P., see Voigt, A. 166 (1996) 694
Strunk, H.P., see Christiansen, S. 166 (1996) 848
Su, C.-H., see Chen, K.-T. 166 (1996) 731
Su, C.-H., Y.-G. Sha, K. Mazuruk, S.L. Lehoczky, H.-C. Liu, R. Fang and R.F.

Brebrick, Mass flux and partial pressures of ZnSe by physical vapor transport 166 (1996) 736
Suemoto, Y., see Obara, K. 166 (1996) 136
Suemoto, Y., see Obara, K. 166 (1996) 271
Sugawara, Y., see Kitamura, T. 166 (1996) 854
Sugino, T., M. Maeda, K. Kawarai and J. Shirafuji, Low-temperature epitaxial growth of InP by remote plasma-assisted metalorganic chemical vapour deposition 166 (1996) 628
Sun, Y., see Yu, X. 166 (1996) 195
Suzuki, T., see Kanda, I. 166 (1996) 669
Suzuki, T., K.-I. Yumoto, M. Hasegawa and H. Takei, In situ observation of phase changes by X-ray diffraction in the Bi–Sr–Ca–Cu–O system 166 (1996) 872
Suzuki, Y., see Kurihara, K. 166 (1996) 904

Tabeling, P., see Emsellem, V. 166 (1996) 251
Tachibana, M., M. Michiyama, H. Sakuma, K. Kikuchi, Y. Achiba and K. Kojima, Growth, perfection, and mechanical properties of $C_{60}$ single crystals 166 (1996) 883
Tadano, A., M. Asanuma and R. Aogaki, Electrochemical nucleation induced by nonequilibrium fluctuations 166 (1996) 1111
Tagami, M., see Yamada, Y. 166 (1996) 804
Tai, C.Y., C.-Y. Shih and W.-S. Juang, Suspension crystallization of p-dichlorobenzene from the melt 166 (1996) 1040
Takagi, Y., see Matsuoka, M. 166 (1996) 1035
Takahashi, H., see Oka, K. 166 (1996) 380
Takahashi, I., see Itoh, Y. 166 (1996) 61
Takahashi, I., see Shimura, T. 166 (1996) 786
Takei, H., see Zhao, T.-r. 166 (1996) 408
Takei, H., see Suzuki, T. 166 (1996) 872
Takiyama, H., see Matsuoka, M. 166 (1996) 1035
Takizawa, T., see Matsushita, H. 166 (1996) 712
Tamiya, A., see Mizuno, K. 166 (1996) 146
Tanabe, K. and M. Shiojiri, Epitaxial growth of indigoid dyes on oriented polyethylene films 166 (1996) 935
Tanaka, S., T. Ishikawa and M. Hibino, Transmission electron microscopy study of InGaAsP/InGaP thin-layer structure grown by liquid phase epitaxy 166 (1996) 334
Tanaka, S., see Yamada, Y. 166 (1996) 804
Tanaka, S., see Kitamura, T. 166 (1996) 854
Tang, D., see Zhong, W. 166 (1996) 91
Taniuchi, T., see Kawaguchi, T. 166 (1996) 489
Taniuchi, T., see Kawaguchi, T. 166 (1996) 493
Tanneberger, U., R. Lacmann, A. Herden, H. Klapper, D. Schmiemann, R.A. Becker, A. Mersmann and U. Zacher, The dispersion of growth rate as a result of different crystal perfection 166 (1996) 1074
Tao, X.T., see Yuan, D.R. 166 (1996) 545
Tarelho, L.V.G., see Ranieri, I.M. 166 (1996) 423
Tatsuoka, H., H. Kuwabara, M. Oshita, T. Nakamura, H. Fujiyasu and Y. Nakanishi, Epitaxial ferromagnetic MnSb layers on GaAs substrates grown by hot-wall epitaxy 166 (1996) 754
Tavare, N.S., see Colônia, E.J. 166 (1996) 976
Tedenac, J.C., see Tomasini, P. 166 (1996) 590
Tegetmeier, A., see Cröll, A. 166 (1996) 239
Tegetmeier, A., A. Cröll, A. Danilewsky and K.W. Benz, GaSb: surface tension and floating-zone growth 166 (1996) 651
Thirumavalavan, M., see Fornari, R. 166 (1996) 572
Tochihara, H., see Hasegawa, T. 166 (1996) 314
Tomasini, P., A. Haidoux, M. Maurin and J.C. Tedenac, Growth by OMVPE and X-ray analysis of ZnTe and ZnTe/ZnSe epilayers on III–V substrates 166 (1996) 590
Tomokage, H., see Kanda, T. 166 (1996) 663
Torrent-Burgués, J., see Gómez-Morales, J. 166 (1996) 1020
Tsvetkov, D., see Dmitriev, V. 166 (1996) 601
Tyurikov, V., see Isaenko, L. 166 (1996) 502

Udaka, T., see Yase, K. 166 (1996) 946
Ulbert, Zs., see Farkas, B. 166 (1996) 1064
Ulrich, J., see Momonaga, M. 166 (1996) 1053
Umeno, M., see Shimura, T. 166 (1996) 786
Uno, T., see Yase, K. 166 (1996) 942
Unoki, H., see Oka, K. 166 (1996) 380
Uusi-Penttilä, M. and K.A. Berglund, Spectroscopic monitoring of environmentally benign anti-solvent crystallization 166 (1996) 967

Valarelli, J.V., see Giulietti, M. 166 (1996) 1089
Van den Bogaert, N. and F. Dupret, Simulation of back-melting in Czochralski growth 166 (1996) 446
Van den Bogaert, N., see Dornberger, E. 166 (1996) 452
Van der Berg, A.C.J.F., see van Enckevort, W.J.P. 166 (1996) 156
Van der Eerden, J.P., see Huitema, E. 166 (1996) 141
Vanderschueren, A., see Stassen, S. 166 (1996) 281
Vandewalle, N., see Cloots, R. 166 (1996) 816
Van Enckevort, W.J.P., A.C.J.F. van der Berg, K.B.G. Kreuwel, A.J. Derksen and M.S. Couto, Impurity blocking of growth steps: experiments and theory 166 (1996) 156
Van Enckevort, W.J.P., see Schermer, J.J. 166 (1996) 622
Van Gelder, R.N.M.R., K.J. Roberts, J. Chambers and T. Instone, Nucleation of single and mixed straight chain surfactants from dilute aqueous solutions 166 (1996) 189
Van Leeuwen, M.L.J., O.S.L. Bruinsma and G.M. van Rosmalen, Three-zone approach for precipitation of barium sulphate 166 (1996) 1004
Van Rosmalen, G.M., see Domingo, C. 166 (1996) 989
Van Rosmalen, G.M., see van Leeuwen, M.L.J. 166 (1996) 1004
Van Rosmalen, G.M., see Ó Meadhra, R. 166 (1996) 1046
Van Rosmalen, G.M., see Kramer, H.J.M. 166 (1996) 1084
Van Scyoc, J.M., R.B. James, T.E. Schlesinger, T.S. Gilbert and M. Schieber, Characterization of silver impurities in mercuric iodide

and their relationship to γ-ray-detector performance 166 (1996) 384
Veciana, J., see Figueras, A. 166 (1996) 798
Ven Graitis, A.J., see Fratello, V.J. 166 (1996) 878
Vidal, A., see Figueiredo, J.M.A. 166 (1996) 222
Vieira Jr., N.D., see Baldochi, S.L. 166 (1996) 375
Vieira, Jr., N.D., see Ranieri, I.M. 166 (1996) 423
Vieira, M.M.F., see Baldochi, S.L. 166 (1996) 375
Viraphong, O., see Oçafrain, A. 166 (1996) 414
Voigt, A., B. Steiner, W. Dorsch, J. Krinke, M. Albrecht, H.P. Strunk and G. Wagner, Solution growth of silicon on multicrystalline Si substrate: growth velocity, defect structure and electrical activity 166 (1996) 694
Volkozub, A.V., see Chowdhury, A.J.S. 166 (1996) 863
Von Ammon, W., see Dornberger, E. 166 (1996) 452

Wagner, G., see Voigt, A. 166 (1996) 694
Wan, P., see Lei, X.-Y. 166 (1996) 909
Wang, M., see Ando, Y. 166 (1996) 888
Wang, W.S., see Aggarwal, M.D. 166 (1996) 542
Wanklyn, B.M.R., see Chowdhury, A.J.S. 166 (1996) 863
Watanabe, T., see Morita, S. 166 (1996) 370
Wei, Q.-H., see Lei, X.-Y. 166 (1996) 909
Weinert, B., see Müller, M. 166 (1996) 636
Weise, S., E. Nowak, A. Lenz, B. Schumann and V. Krämer, Investigations of the system $LiInSe_2$–$CuInSe_2$ 166 (1996) 718
Weiss, E., E. Benory, E. Kedar, Y. Juravel and A. Frenkel, Is $Hg_{1-x}Cd_xTe$ grown epitaxially by the travelling heater method? Does it matter? 166 (1996) 745
Wetter, N.U., see Ranieri, I.M. 166 (1996) 423
Wetzel, G., see Rossberg, A. 166 (1996) 354
Wilson, G.A., see Morris Hotsenpiller, P.A. 166 (1996) 779
Wolf, Th., Crystal growth mechanisms and growth anisotropy of $YBa_2Cu_3O_x$ crystals 166 (1996) 810
Woos, B.W., see De Yoreo, J.J. 166 (1996) 291
Wu, K. and C. Chen, Theoretical studies for novel non-linear optical crystals 166 (1996) 533

Xia, C.-T., E.-W. Shi, W.-Z. Zhong and J.-K. Guo, Hydrothermal synthesis of $BaTiO_3$ nano/microcrystals 166 (1996) 961
Xu, D., see Yuan, D.R. 166 (1996) 545
Xu, J.-j., Global interfacial instabilities and selection of dendrite growth 166 (1996) 201

Yamada, T., see Schäfer, N. 166 (1996) 675
Yamada, Y., M. Nakamura, C. Krauns, M. Tagami, Y. Shiohara and S. Tanaka, Top-seeded solution growth of $YBa_2Cu_3O_{6+d}$ superconductive crystals 166 (1996) 804
Yamada, Y., see Kitamura, T. 166 (1996) 854
Yamada, Y., see Nakamura, M. 166 (1996) 859
Yamaguchi, H., see Oka, K. 166 (1996) 380
Yang, G., J.S. Abell, P. Shang, I.P. Jones and C.E. Gough, Growth and microstructure in $Bi_2Sr_2CaCu_2O_y$ single crystals 166 (1996) 820
Yaroslavsky, Y., see Burtman, V. 166 (1996) 832
Yase, K., Y. Yoshida, T. Uno and N. Okui, Direct analysis of an organic molecular beam by quadrupole mass spectrometry 166 (1996) 942
Yase, K. and T. Udaka, Two-dimensional crystallization of ferritin molecules at the air–water interface 166 (1996) 946
Yasuda, K., H. Hatano, T. Ferid, M. Minamide, T. Maejima and K. Kawamoto, Growth characteristics of (100)HgCdTe layers in low-temperature MOVPE with ditertiarybutyltelluride 166 (1996) 612
Yoda, S., see Kinoshita, K. 166 (1996) 266
Yoshida, Y., see Yase, K. 166 (1996) 942
Yu, X., Y. Sun, H. Jiang and S. Zhang, Growth kinetics of the metastable tetragonal phase of potassium dideuterium phosphate (DKDP) crystals 166 (1996) 195
Yuan, D.R., N. Zhang, X.T. Tao, D. Xu, M.G. Liu, W.B. Hou, Y.H. Bing and M.H. Jiang, Growth of a new highly efficient organic nonlinear optical crystal: 3-methoxy-4-hydroxy-benzaldehyde (MHBA) 166 (1996) 545
Yumoto, K.-I., see Suzuki, T. 166 (1996) 872

Zacher, U., see Tanneberger, U. 166 (1996) 1074
Zaitseva, N.P., see Smolsky, I.L. 166 (1996) 228
Zaitseva, N.P., see De Yoreo, J.J. 166 (1996) 291
Zanotti, L., see Zeng, L. 166 (1996) 528
Zanotti, L., see Carrà, S. 166 (1996) 641
Zappettini, A., see Fornari, R. 166 (1996) 572
Zemke, D., see Amon, J. 166 (1996) 646
Zeng, L., M. Zha, M. Ardoino, P. Franzosi, L. Zanotti, G. Zuccalli and C. Paorici, Solution crystal growth of urea and derivatives for nonlinear optical applications 166 (1996) 528
Zezell, D.M., see Ranieri, I.M. 166 (1996) 423
Zha, M., see Zeng, L. 166 (1996) 528
Zhang, H., see Zou, Y.F. 166 (1996) 476
Zhang, N., see Yuan, D.R. 166 (1996) 545
Zhang, S., see Yu, X. 166 (1996) 195
Zhang, Y., see Chen, K.-T. 166 (1996) 731
Zhao, T.-r., M. Hasegawa and H. Takei, Crystal growth and characterization of cuprous ferrite ($CuFeO_2$) 166 (1996) 408
Zhong, W. and D. Tang, Growth units and morphology of lithium triborate (LBO) crystals 166 (1996) 91
Zhong, W.-Z., see Xia, C.-T. 166 (1996) 961
Zhou, C.-H., see Lei, X.-Y. 166 (1996) 909
Zou, Y.F., H. Zhang and V. Prasad, Dynamics of melt–crystal interface and coupled convection–stress predictions for Czochralski crystal growth processes 166 (1996) 476
Zubrilov, A., see Dmitriev, V. 166 (1996) 601
Zuccalli, G., see Zeng, L. 166 (1996) 528
Zyss, J., see Gauvin, S. 166 (1996) 507

ELSEVIER

Journal of Crystal Growth 166 (1996) 1137–1140

JOURNAL OF CRYSTAL GROWTH

# Subject index

Apparatus
– for melt growth
– – by Bridgman–Stockbarger method
– – – of gallium arsenide 566
– for organic crystalline thin films 507
– for miscellaneous purposes
– – fibre growth of uranium under ultrahigh vacuum 394
– – in situ X-ray and microscopic observation 872
– – quadrupole analysis of organic molecular beams 942
– – ultrasoft X-ray absorption 67

Cadmium
– sulphide 731
– telluride 245
– telluride selenide 256
Calcium
– fluoride 61
Cellular growth
– of gamma-aminobutyric acid 104
– of nematic isotropic interface 222
Characterization
– by Michelson interferometry
– – of canavalin 913
Cobalt 792
Computer simulation
– of heat convection 463
– of impurity blocking 156
– of industrial crystallizer 1084
– of melt crystal interface 476
– of supercooling of melts 578
– of surface relaxation on morphology 84
– of surface roughening 17
– of thermal capillary problem 458
– of transient thermal dynamics 452
Constitutional supercooling
– of lithium lead phosphate 361
Convection 124, 136, 239, 261, 266, 303, 700, 825
Copper
– indium selenide 708

Defects
– in aluminum 146
– in lithium niobate 151
– of hair-like inclusion in potassium dihydrogen phosphate 228
– theory of formation 141

Dendritic growth
– of ammonium bromide 251
– of xenon 207, 212
– theory of global interfacial instability 201
– theory of three-dimensional model 339
Device characterization
– diodes 601, 745
– electronic materials 245, 325, 329, 572, 745
– heterojunction 309, 334
– infrared detectors 745
– optical crystals 291
– piezoelectric 347
– radiation sensors 256, 384
– scintilators 419
– wave guides 489
Diamond 675
Diffusional control
– of oxygen in silicon 183
Diodes, see Device characterization
Dissolution
– of gamma-aminobutyric acid 104
– of nitrogen in gallium 583
– of rare earth ortho-ferrites 109

Electronic materials, see Device characterization
Epitaxy, see Thin film growth
Etching
– chemical 319, 641, 883
– thermal 167
Eutectic growth
– of tin selenide 398

Gallium
– antimonide 651
– arsenide 72, 217, 239, 309, 636, 641, 646
– nitride 597, 601
– ortho-phosphate 347
– phosphide 309
Growth theory
– ab initio prediction of polymorphs 900
– dispersion of growth rate 107
– of dissolution rates by reaction fractal dimensions 1053
– of Hartman–Perdok 17
– of lamellar eutectics 29
– of levitated microdroplets 981

– of solute distribution 483
– of suspension mixing 1064

Heterojunction, see Device characterization
Hydrodynamics, see Convection

Indium
– gallium arsenide 463
– gallium arsenide phosphide 334
– phosphide 309, 628, 646
Industrial crystallization
– of ammonium chloride 1099
– of potassium sulphate 1105
Infrared detectors, see Device characterization

Kinetics
– of growth 91, 104, 112, 117, 124, 129, 136, 156, 162, 179, 195, 271, 303, 347, 469, 578, 763, 810, 893, 904, 946, 976, 1004, 1020, 1040, 1046, 1094, 1099
– of interface control 61, 67, 222, 303, 854
– of melt structure 578
– of nucleation 179, 271, 841, 961, 976, 1020, 1046, 1058, 1094, 1099, 1111
– of purification 998

Lasers, crystals for
– barium lithium fluoride 375
– lithium yttrium fluoride 423
– nonlinear optics 533
Lead
– bromide 266, 364
Lysozyme 40, 904, 919

Melt growth technique
– by Bridgman–Stockbarger method
– – of cobalt triantimonide 722
– – of copper indium selenide 708
– – of germanium 700
– – of lead bromide 364
– – of potassium magnesium fluoride 419
– – of rhodium triantimonide 722
– – of tin selenide 398
– – of 2-dicyanovinylanisole 542
– – – theory of convention 436
– by Czochralski method
– – of barium lithium fluoride 375
– – of barium metaborate 497
– – of bismuth silicon oxide 325
– – of gallium arsenide 636, 641
– – of garnets 774
– – of indium phosphide 303, 572
– – of iron based compound by cold crucible 298
– – of iron titanium 390
– – of lithium lead phosphate 361
– – of lithium niobate in high magnetic field 286
– – of neodymium strontium galate 825
– – of nickel perovskites 878
– – of perovskite rare earth aluminate 370
– – of praseodymium strontium galate 825
– – of rare earth tantalates 303
– – of rutile in high magnetic field 286
– – of silicon 183, 469, 663, 669, 680
– – of silicon germanium 657
– – of yttrium lithium fluoride 423
– – theory of back melting 446
– by floating zone method
– – of cuprous ferrite 408
– – of gallium antimonide 319
– – of gallium arsenide 239
– – of lithium niobate 151
– – of silicon 319
– by inverted bell temperature profile
– – of organic crystalline films 507
– by liquid feeding Czochralski method
– – of silicon 685
– by micro-pulling down method
– – of silicon germanium 675
– by Stephanov method
– – of tin 458
– by suspensive crystallization
– – of p-dichloro benzene 1040
– by top seeded method
– – of barium titanate 550
– by uniaxial solidification
– – of lithium zinc arsenide 631
– – of sodium magnesium fluoride 414
– – of sodium nitrate 483
– – of xenon dendrites 212
– by vertical gradient freeze
– – of gallium arsenide 646
– – of indium phosphide 646
Mercury
– iodide 354
Microgravity, growth under
– of cadmium telluride 245
– of cadmium telluride selenide 256
– of gallium antimonide 651
– of gallium arsenide 239
– of lead bromide 266
– of lead chloride 266
– of silicon 319
Monte Carlo simulation
– of Lennard-Jones potential 141
Morphological stability
– of copper sulphate pentahydrate 1089
– of electrodeposition of metal and organic polymers 276
– of lithium triborate 91
– of 6-amino penicilanic acid 1078

Nucleation
– of calcium carbonate 1015
– of drop-like clusters 909
– of excess vacancies 146
– of J-aggregates 930
– of potash alum 1068

Numbers
– fractal dimension 207
– Grashof 476, 669, 700
– Peclet 251
– Reynolds 669

Optical crystals, see Device characterization

Phase diagram
– of aluminum nitride 583
– of copper gallium indium selenide 712
– of copper indium selenide 718
– of gallium nitride 583
– of indium nitride 583
– of iron titanate 390
– of lanthanum strontium galate 825
– of lead titanate 380
– of lithium indium selenide 718
– of PrYBCO 804
– of samarium barium cobalt 859
– of tin selenide 398
– of YBCO 804
Precursor
– for copper indium selenide 708
– for metalorganic chemical vapor deposition 832
– for nonlinear optical organics 507
– for rutile 763
Purification of materials
– of copper 708
– of isomers 976
– of lead iodide 384
– of mercury iodide 384
– of organic solution 1035
– of proteins 40

Silicon 183, 314, 319, 469, 617, 663, 669, 680, 685, 727
– carbide 607
– dioxide 727, 786
– germanium 657, 675, 727
Solid growth technique
– by polymorphic transformation
– – of L-glutamic acid 129
– by recrystallization
– – of aluminum 146
– – of BSCCO 863
Solution growth technique
– by antisolvent crystallization
– – of lysine manohydrochloride 967
– by aqueous solution
– – of barium sulphate 1004
– – of calcium carbonate 1015, 1020
– – of chlorobenzoic 976
– – of ferritin molecules 946
– – of pentaerythritol 1046
– – of potassium chromate 156
– – of potassium dideuterium phosphate 195
– – of potassium dihydrogen phosphate 228, 291
– – of sodium laurate 189
– – of sodium myristate 189
– – of strontium sulphate 998
– – of tetracosane 1094
– by centrifugal techniques
– – of gallium arsenide 234
– – of germanium 234
– – of silicon germanium 234
– by colloidal chemistry
– – of lead sulphide 769
– by electrocrystallization
– – of zinc oxide 1116
– by flux method
– – of BSCCO 820
– – of cesium titryl arsenate 537
– – of chromium borides 429
– – of cobalt substituted M-hexaferrite 402
– – of rubidium titryl arsenate 537
– – of tin substituted M-hexaferrite 402
– – of YBCO 810
– by gel method
– – of ammonium bromide 251
– – of barium titanate 550
– – of silica 996
– by high pressure nitrogen
– – of gallium nitride 583
– – theory of solute diffusivity 261
– by hydrothermal growth
– – of barium titanate 961
– – of gallium ortho-phosphate 347
– by low temperature method
– – of E-2-butenedeioce acid 179
– – of lansine complex 925
– – of meta-chloro nitro benzene 971
– – of monomethyl urea 528
– – of potassium hydrogen tartrate 172
– – of proteins 40
– – of 3-methoxy-4-hydroxy-benzaldehyde 545
– – of urea 528
– by mixing
– – of oxazolin compounds 1027
– by rapid expansion of supercritical solution
– – of benzoic acid 989
– by seeding system
– – of alumina trihydrate 1009
– – of aluminum hydroxide 1009
– by temperature difference method
– – of indium gallium arsenide 463
– by top seeded method
– – of lead titanate 380
– – of lithium lead phosphate 380
– – of PrYBCO 804
– – of YBCO 804
– by travelling heater method
– – of cadmium telluride 245
– – of mercury cadmium telluride 745
Statistical mechanics, molecular theory
– of inhomogeneous cell model 112, 117

Stefan problem or moving boundary problem
– of crystal pulling 458
– of nematic-isotropic interface 222
Superconductivity materials, high $T_c$
– bulk
– – of BSCCO 281, 820, 863, 867
– – of PrYBCO 804
– – of YBCO 804, 810, 816
– film
– – of YBCO 832, 836, 841, 848, 854
Surface energy, determination
– of potassium dihydrogen phosphate 162
Surface morphology
– of helium 4 crystals 55
– of lithium niobate 1
– of silicon observed by high temperature 314
Surface structure
– of calcium fluoride 61
– of canavalin protein 893
– of carbon nanotubes 888
– of gallium arsenide 72
– of n-alkanes 67
– of rutile 763
– of silicon 617

Thin film growth, epitaxy
– by direct current biased sputter deposition
– – of cobalt 792
– by ion beam sputter deposition
– – of rutile 779
– by liquid phase epitaxy
– – of BSCCO 867
– – of cyamine dye 930
– – of garnets 774
– – of indium gallium arsenide phosphide 334
– – of lithium niobate 489, 493
– – of lithium tantalate 489
– – of silicon 694, 727
– – of silicon carbide 607
– – of silicon dioxide 727
– – of silicon germanium 727
– – of YBCO 836, 854
– by molecular beam epitaxy
– – of calcium fluoride 61
– – of gallium arsenide 72, 217
– – of gallium nitride 597, 601
– – of silicon 314
– – theory of thermal etching of III–V compounds 167
– by pulsed electron-beam evaporation
– – of TBCO 848
– by vapor phase epitaxy
– – through chemical vapor deposition
– – – of diamond 622
– – – of poly-silicon 689
– – – of silicon 329
– – – of tetrathiafulvalene–tetracyanoquinodimethane 798
– – through metalorganic chemical vapor deposition
– – – of cadmium selenide 558
– – – of gallium antimonide 590
– – – of gallium arsenide 309
– – – of gallium nitride 601
– – – of gallium phosphide 309
– – – of indium phosphide 309, 590, 628
– – – of lithium niobate 1
– – – of mercury cadmium telluride 612
– – – of rutile 763
– – – of silicon 1
– – – of yttrium barium cuprates 841
– – – of zinc selenide 558, 590
– – – of zinc sulphide 558
– – – of zinc telluride 590

Vapor growth technique
– by chemical vapor deposition
– – of transition metal phosphide 99
– by evaporation and condensation
– – of fullerene 883
– – of manganese antimonide 754
– – of mercuric iodide 354
– – of niobium 271
– by physical vapor transport
– – of cadmium sulphide 731
– – of zinc selenide 736
– theory of diffusion 739
Vapor–liquid–solid growth
– of water 124

Whisker growth
– of alpha-zinc phosphide 99
– of beta-titanium phosphide 99